

NONVOLATILE SEMICONDUCTOR MEMORY DEVICE

Abstract

An object of the present invention is to provide a nonvolatile semiconductor memory device having a storage region constructed by a plurality of electrically rewritable nonvolatile memory cells and a booster circuit for boosting a power source voltage to thereby generate a voltage necessary to rewrite the storage region, wherein the power source voltage can be prevented from being decreased in the device and data in the storage region can be stably rewritten. The nonvolatile semiconductor memory device has a voltage determining part (38) for determining a voltage level of a predetermined node in the semiconductor memory device in rewriting of the storage region (24), and a rewrite unit determining part (44) for determining the number of bits of input data to be rewritten at once on the basis of a result of determination of the voltage determining part (38).

Reference Drawing: FIG. 1